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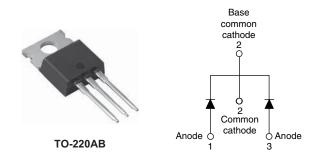
VS-MUR2020CTPbF, VS-MUR2020CT-N3

Vishay Semiconductors

RoHS

COMPLIANT

Ultrafast Rectifier, 2 x 10 A FRED Pt[®]



PRODUCT SUMMARY							
Package	TO-220AB						
I _{F(AV)}	2 x 10 A						
V _R	200 V						
V _F at I _F	See Electrical table						
t _{rr} typ.	See Recovery table						
T _J max.	175 °C						
Diode variation	Common cathode						

FEATURES

- Ultrafast recovery time
- Low forward voltage drop
- 175 °C operating junction temperature
- Low leakage current
- Compliant to RoHS Directive 2002/95/EC
- Designed and qualified according to HALOGEN
 JEDEC-JESD47
 HALOGEN
 Available
- Halogen-free according to IEC 61249-2-21 definition
 (-N3 only)

DESCRIPTION/APPLICATIONS

VS-MUR2020CTPbF is the state of the art ultrafast recovery rectifier specifically designed with optimized performance of forward voltage drop and ultrafast recovery time.

The planar structure and the platinum doped life time control, guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS								
PARAMETER		SYMBOL	TEST CONDITIONS	MAX.	UNITS			
Peak repetitive reverse voltage		V _{RRM}		200	V			
Average restified forward ourrest	per leg	I _{F(AV)}		10				
Average rectified forward current	total device		Rated V _R , T _C = 145 °C	20	۸			
Non-repetitive peak surge current per leg		I _{FSM}		100	A			
Peak repetitive forward current per leg		I _{FM}	Rated V _R , square wave, 20 kHz, $T_C = 145 \text{ °C}$	20				
Operating junction and storage temperatures		T _J , T _{Stg}		- 65 to 175	°C			

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	200	-	-		
Forward voltage V _F		I _F = 8 A, T _J = 125 °C	-	-	0.85	V	
	V _F	I _F = 16 A	-	-	1.15		
		I _F = 16 A, T _J = 125 °C	-	-	1.05		
Povorao lookogo ourrant		V _R = V _R rated	-	-	15		
Reverse leakage current		$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	-	250	μA	
Junction capacitance	CT	V _R = 200 V	-	55	-	pF	
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8.0	-	nH	

Revision: 11-Aug-11

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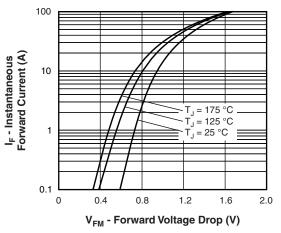
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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS		
		$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t =$	50 A/µs, V _R = 30 V	-	-	35			
Reverse recovery time	t _{rr}	I _F = 0.5 A, I _R = 1.0 A, I _{REC} = 0.25 A		-	-	25	ns		
Reverse recovery time		T _J = 25 °C	I _F = 10 A dI _F /dt = 200 A/μs V _R = 160 V	-	21	-	115		
		T _J = 125 °C		-	35	-			
Pook receivery ourrent	1	T _J = 25 °C		-	1.9	-	А		
Peak recovery current	I _{RRM}	T _J = 125 °C		-	4.8	-			
Deverse weeks where	0	T _J = 25 °C		-	25	-			
Reverse recovery charge	Q _{rr}	T _J = 125 °C		-	78	-	nC		

THERMAL - MECHANICAL SPECIFICATIONS								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Maximum junction and storage temperature range	T _J , T _{Stg}		- 65	-	175	°C		
Thermal resistance, per leg	Р		-	-	2.5			
junction to case total device	R _{thJC}		-	-	1.25			
Thermal resistance, junction to ambient per leg	R _{thJA}		-	-	50	°C/W		
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.5	-			
Weight			-	2.0	-	g		
Weight			-	0.07	-	oz.		
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)		
Marking device		Case style TO-220AB	MUR2020CT					

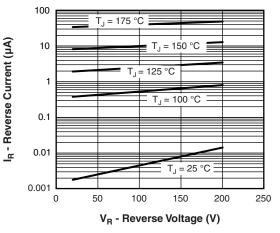
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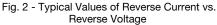




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Fig. 1 - Maximum Forward Voltage Drop Characteristics





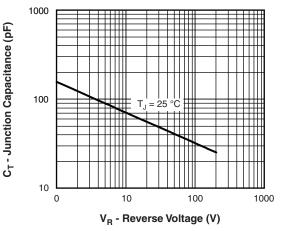


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

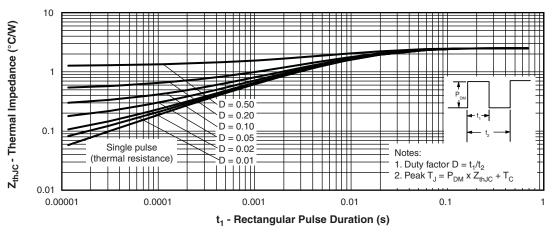
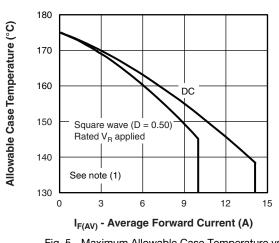


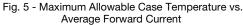
Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics



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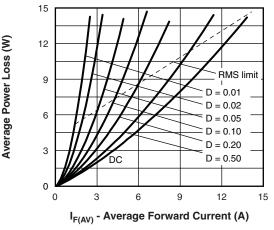
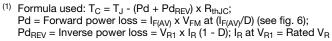


Fig. 6 - Forward Power Loss Characteristics

Note



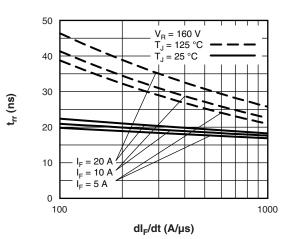
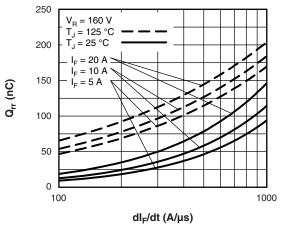


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt





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VS-MUR2020CTPbF, VS-MUR2020CT-N3

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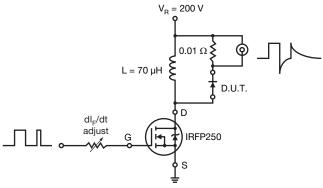
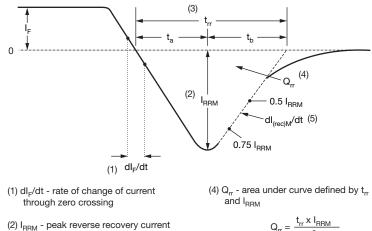


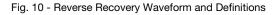
Fig. 9 - Reverse Recovery Parameter Test Circuit



$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(3) t_{rr} - reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.

(5) $dI_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}





VS-MUR2020CTPbF, VS-MUR2020CT-N3

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ORDERING INFORMATION TABLE

Device code	VS-	MUR	20	20	СТ	PbF
		2	3	4	5	6
	1 -		nay Sem			oduct
	2 -		afast Ml		-	
	3 -	Cur	rent rati	ng (20 =	20 A)	
	4 - Voltage rating (20 = 200 V))	
	5 -	СТ	= Cente	r tap (dı	ual)	
	6 -	Env	ironmen	ital digit:		
		PbF	= Lead	(Pb)-fre	e and F	RoHS co

-N3 = Halogen-free, RoHS compliant and totally lead (Pb)-free

ORDERING INFORMATION (Example)							
PREFERRED P/N QUANTITY PER T/R MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION							
VS-MUR2020CTPbF	50	1000	Antistatic plastic tube				
VS-MUR2020CT-N3	50	1000	Antistatic plastic tube				

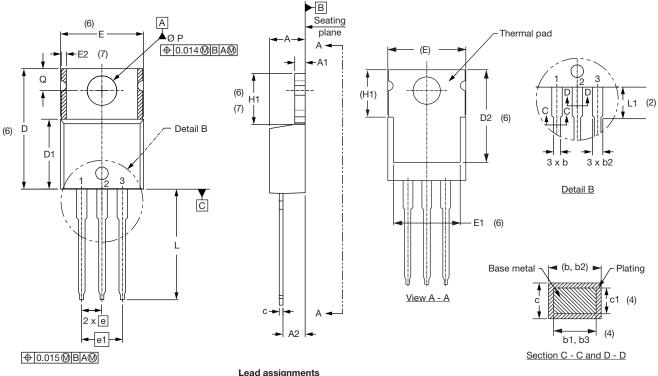
LINKS TO RELATED DOCUMENTS						
Dimensions www.vishay.com/doc?95222						
Davit ve autoir a infance ation	TO-220ABPbF	www.vishay.com/doc?95225				
Part marking information	TO-220AB-N3	www.vishay.com/doc?95028				
SPICE model		www.vishay.com/doc?95272				

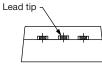


Vishay Semiconductors

TO-220AB

DIMENSIONS in millimeters and inches





.ead	assignments

Diodes

1. - Anode/open 2. - Cathode 3. - Anode

SYMBOL	MILLIN	IETERS	6 INCHES		NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.56	2.92	0.101	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.25	0.585	0.600	3
D1	8.38	9.02	0.330	0.355	
D2	11.68	12.88	0.460	0.507	6

Notes

- ⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994
- ⁽²⁾ Lead dimension and finish uncontrolled in L1
- ⁽³⁾ Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- $^{\left(4\right) }$ Dimension b1, b3 and c1 apply to base metal only
- (5) Controlling dimensions: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2 and E1

MILLIMETERS INCHES SYMBOL NOTES MIN. MAX. MIN. MAX. 10.51 0.414 10.11 0.398 3,6 Е E1 6.86 8.89 0.270 0.350 6 E2 0.76 0.030 7 --2.41 2.67 0.095 0.105 е 0.208 e1 4.88 5.28 0.192 H1 6.09 6.48 0.240 0.255 6,7 13.52 14.02 0.532 0.552 L L1 3.32 3.82 0.131 0.150 2 ØΡ 3.54 3.73 0.139 0.147 2.60 0.102 Q 3.00 0.118 90° to 93° 90° to 93° θ

Conforms to JEDEC outline TO-220AB

- (7) Dimensions E2 x H1 define a zone where stamping and singulation irregularities are allowed
- (8) Outline conforms to JEDEC TO-220, except A2 (maximum) and D2 (minimum) where dimensions are derived from the actual package outline



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